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Triacs

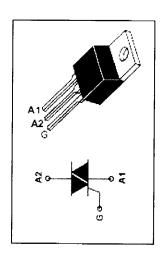
TIC246M

FEATURES

- · With TO-220 package
- Sensitive Gate Triacs
- Glass Passivated
- Max I_{GT} of 50 mA (Quadrants 1~3)

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	MIN	UNIT	
V _{DRM}	Repetitive peak off-state voltage	600 600		
V_{RRM}	Repetitive peak reverse voltage		V	
I _{T(RMS)}	RMS on-state current (full sine wave)T _C =70℃	16	Α	
I _{TSM}	Non-repetitive peak on-state current	125	Α	
Tj	Operating junction temperature	110	°C	
T_{stg}	Storage temperature	-45~125	°C	
R _{th(j-c)}	Thermal resistance, junction to case	1.9	°C/W	
$R_{th(j-a)}$	Thermal resistance, junction to ambient	62.5	°C/W	



ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER Repetitive peak off-state current		CONDITIONS	TYP.	MAX	UNIT
I _{DRM}			V _D =V _{DRM} , T _C =110 °C		2.0	mA
I _{GT}	Gate trigger current	I	V _{supply} = 12 V†; R _L = 10 Ω; t _{p(g)} >20 μ s	12	50	mA
		II		19	50	
		III		16	50	
		IV		34		
Iн	Holding current		$V_{\text{supply}} = 12 \text{ V}^{\dagger}, I_{\text{G}} = 0 \text{ initial } I_{\text{TM}} = 100 \text{mA}$		40	mA
V_{GT}	Gate trigger voltageall quadrant		$V_{\text{supply}} = 12 \text{ V}$; $R_L = 10 \Omega$; $t_{p(g)} > 20 \mu \text{ s}$		2	V
V _{TM}	On-state voltage		I _T = 22.5A; I _G = 50mA		1.7	V

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